a fourth device region of the first conductivity type provided in said second well, said third and fourth device regions being disposed not to oppose each other face-to-face, with a second section of said well isolation structure disposed between said third and fourth device regions, said fourth device region being ~~provided~~ positioned separately from and adjacent to said second device region;

wherein said second section of said well isolation structure is wider than said first section of said well isolation structure. ~~a first width of said well isolation structure between said first and second device regions is smaller than a second width of said well isolation structure between said third and fourth device regions.~~

Claim 17 (currently amended)The semiconductor device according to claim 16, wherein said first, second, third and fourth device regions have a substantially same ~~configuration~~ shape.

Claim 18 (currently amended)A semiconductor device comprising:

a first well of p type and a second well of n type disposed adjacent to each other;

a straight well isolation structure comprising a shallow trench formed on a boundary of said first and second wells;

a pair of a first device region of n type and a second device region of p type, said first and second device regions being disposed to oppose each other face-to-face, with a first section of said well isolation structure disposed between said first device region and said second device region;

a third device region of n type and fourth device region of p type, said third and fourth device regions being disposed not to oppose each other face-to-face, with a second section of said well isolation structure disposed between said third device region and said fourth device region;

wherein said first and third device regions are adjacent to each other and separately ~~provided~~ positioned in said first well, and said ~~third~~ second and fourth device regions are adjacent to each other and separately ~~provided~~ positioned in said second well, and ~~a first width~~ said second section of said well isolation structure ~~between said~~

~~first and second device regions~~ is ~~smaller~~ wider than ~~a~~ said ~~second~~ first section of said well isolation structure ~~between said third and fourth device regions~~.

Allowable Subject Matter

2. Claims 16-18 are allowed.

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. References A-C are cited as being related to a trench isolation structure.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shouxiang Hu whose telephone number is 571-272-1654. The examiner can normally be reached on Monday through Thursday, 7:30 AM to 6:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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SH
March 17, 2004

SHOUXIANG HU
PRIMARY EXAMINER